

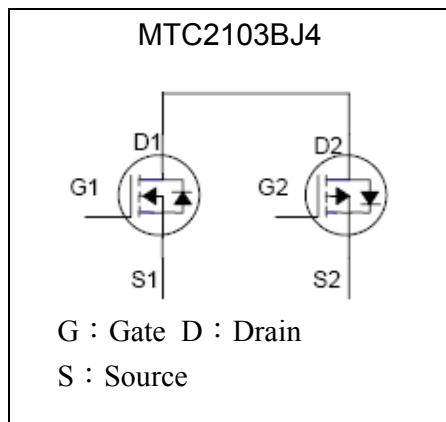
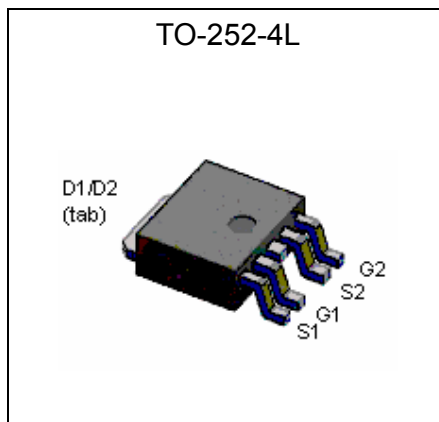
N & P-Channel Enhancement Mode Power MOSFET

MTC2103BJ4

	N-CH	P-CH
BV_{DSS}	30V	-30V
I_D	8A	-6A
$R_{DS(on)(MAX)}$	21m Ω	45m Ω

Features

- Low Gate Charge
- Simple Drive Requirement
- 100% UIS test @ $V_D=15V$, $L=0.1mH$, $V_G=10V$, $I_L=7.5A$, Rated $V_{DS}=30V$, for N-CH
- 100% UIS test @ $V_D=15V$, $L=0.1mH$, $V_G=-10V$, $I_L=-6A$, Rated $V_{DS}=-30V$, for P-CH
- RoHS compliant & Halogen-free package

Equivalent Circuit

Outline

Absolute Maximum Ratings ($T_c=25^\circ C$, unless otherwise noted)

Parameter	Symbol	Limits		Unit
		N-channel	P-channel	
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	
Continuous Drain Current @ $T_c=25^\circ C$	I_D	8	-6	A
Continuous Drain Current @ $T_c=100^\circ C$	I_D	6	-5	
Pulsed Drain Current *1	I_{DM}	32	-24	
Avalanche Current	I_{AS}	15	-15	mJ
Avalanche Energy @ $L=0.1mH$, $I_D=10A$ (-10A for P-ch), $R_G=25\Omega$	E_{AS}	5	5	
Repetitive Avalanche Energy @ $L=0.05mH$ *2	E_{AR}	2.5	2.5	
Total Power Dissipation ($T_c=25^\circ C$)	P_d	25		W
Total Power Dissipation ($T_c=100^\circ C$)		18		
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55~+175		$^\circ C$

Note : *1. Pulse width limited by maximum junction temperature

 *2. Duty cycle $\leq 1\%$



Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	6	$^{\circ}C/W$
Thermal Resistance, Junction-to-ambient, max * 1	$R_{th,j-a}$	90	$^{\circ}C/W$

Note : *1 62.5 $^{\circ}C/W$ when mounted on a 1 in² pad of 2 oz copper.

N-CH Characteristics (Tc=25 $^{\circ}C$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	30	-	-	V	$V_{GS}=0, I_D=250\mu A$
$V_{GS(th)}$	1	1.5	3	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$G_{FS} *1$	-	16	-	S	$V_{DS}=5V, I_D=8A$
I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20, V_{DS}=0$
I_{DSS}	-	-	1	μA	$V_{DS}=24V, V_{GS}=0$
	-	-	25	μA	$V_{DS}=20V, V_{GS}=0, T_j=125^{\circ}C$
$I_{D(ON)} *1$	8	-	-	A	$V_{DS}=10V, V_{GS}=10V$
$R_{DS(ON)} *1$	-	18	21	$m\Omega$	$V_{GS}=10V, I_D=8A$
	-	34	42	$m\Omega$	$V_{GS}=4.5V, I_D=6A$
Dynamic					
$Q_g(V_{GS}=10V)*1$	-	11	-	nC	$I_D=8A, V_{DS}=15V, V_{GS}=10V$
$Q_g(V_{GS}=4.5V)*1$	-	6	-		
$Q_{gs} *1$	-	1.2	-		
$Q_{gd} *1$	-	3.3	-		
$t_{d(ON)} *1$	-	11	-	ns	$V_{DS}=15V, I_D=1A, V_{GS}=10V, R_G=6\Omega$
$t_r *1$	-	16	-		
$t_{d(OFF)} *1$	-	36	-		
$t_f *1$	-	20	-		
C_{iss}	-	1115	-	pF	$V_{GS}=0V, V_{DS}=15V, f=1MHz$
C_{oss}	-	116	-		
C_{rss}	-	82	-		
Source-Drain Diode					
$I_S *1$	-	-	2.3	A	
$I_{SM} *2$	-	-	9.2		
$V_{SD} *1$	-	-	1.2	V	$I_F=I_S, V_{GS}=0V$
$t_{rr} *1$	-	50	-	ns	$I_F=I_S, V_{GS}=0, dI_F/dt=100A/\mu s$
$Q_{rr} *1$	-	2	-	nC	

Note : *1.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

*2.Pulse width limited by maximum junction temperature.



P-CH Characteristics (Tc=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-30	-	-	V	V _{GS} =0, I _D =-250μA
V _{GS(th)}	-1	-1.5	-3	V	V _{DS} =V _{GS} , I _D =-250μA
G _{FS} *1	-	16	-	S	V _{DS} =-5V, I _D =-6A
I _{GSS}	-	-	±100	nA	V _{GS} =±20, V _{DS} =0
I _{DSS}	-	-	-1	μA	V _{DS} =-24V, V _{GS} =0
	-	-	-25	μA	V _{DS} =-20V, V _{GS} =0, T _j =125°C
I _{D(ON)} *1	-6	-	-	A	V _{DS} =-5V, V _{GS} =-10V
R _{DS(ON)} *1	-	36	45	mΩ	V _{GS} =-10V, I _D =-6A
	-	60	76	mΩ	V _{GS} =-4.5V, I _D =-5A
Dynamic					
Q _g (V _{GS} =-10V)*1	-	10	-	nC	I _D =-6A, V _{DS} =-15V, V _{GS} =-10V
Q _g (V _{GS} =-4.5V)*1	-	7.2	-		
Q _{gs} *1	-	2.2	-		
Q _{gd} *1	-	2	-		
t _{d(ON)} *1	-	5.5	-	ns	V _{DS} =-15V, I _D =-1A, V _{GS} =-10V, R _G =6Ω
t _r *1	-	10	-		
t _{d(OFF)} *1	-	28	-		
t _f *1	-	15	-		
C _{iss}	-	1320	-	pF	V _{GS} =0V, V _{DS} =-15V, f=1MHz
C _{oss}	-	500	-		
C _{rss}	-	460	-		
Source-Drain Diode					
I _S *1	-	-	-2.3	A	
I _{SM} *2	-	-	-9.2		
V _{SD} *1	-	-	-1.2	V	I _F =I _S , V _{GS} =0V
t _{rr} *1	-	55	-	ns	I _F =I _S , V _{GS} =0, dI _F /dt=100A/μs
Q _{rr} *1	-	2.2	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
 *2.Pulse width limited by maximum junction temperature.

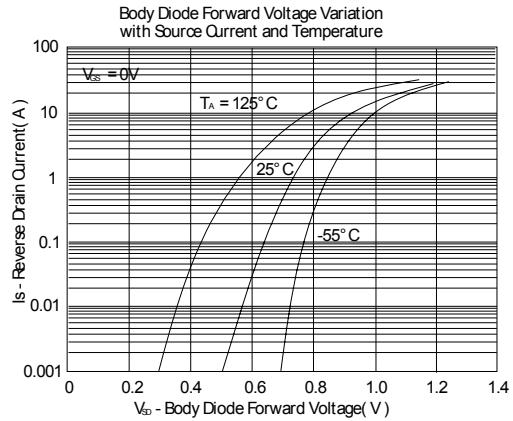
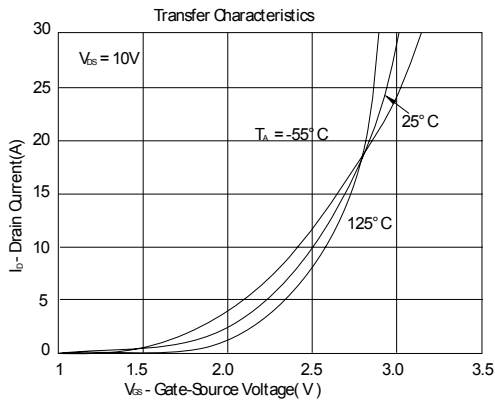
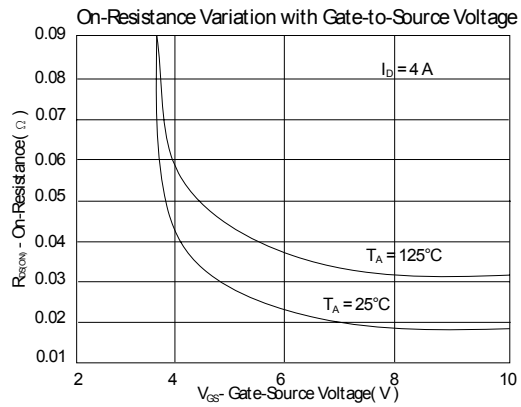
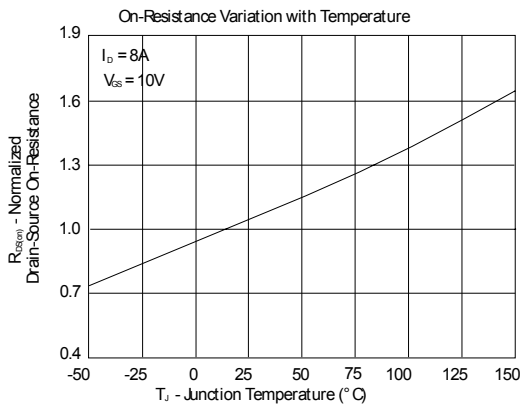
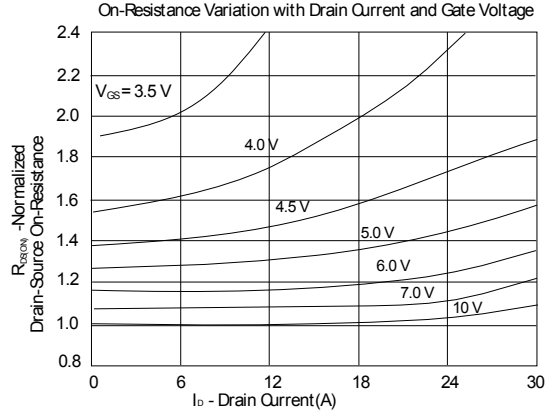
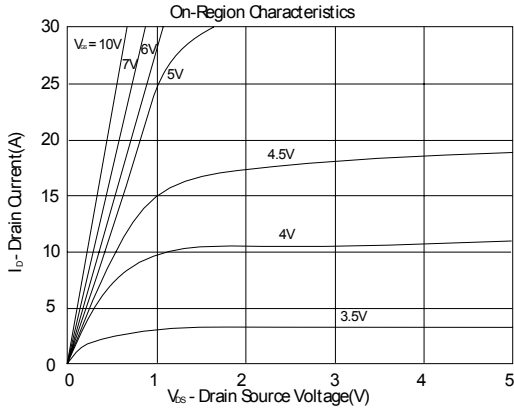
Ordering Information

Device	Package	Shipping	Marking
MTC2103BJ4	TO-252 (RoHS compliant & Halogen-free package)	2500 pcs / Tape & Reel	2103



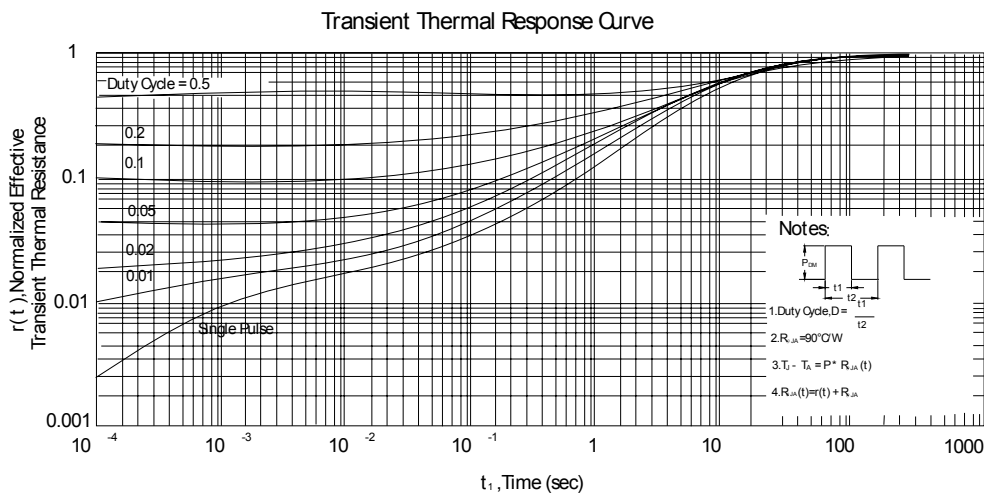
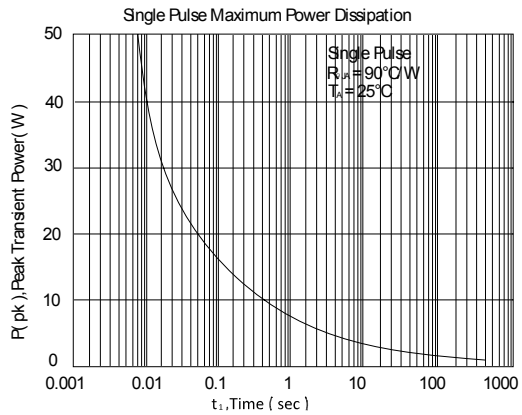
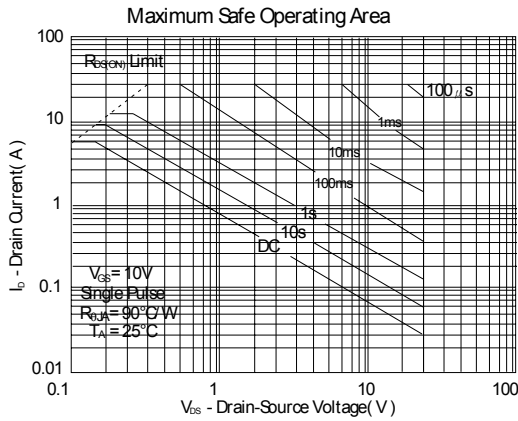
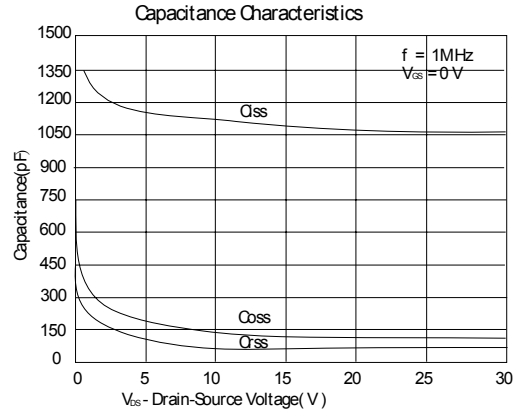
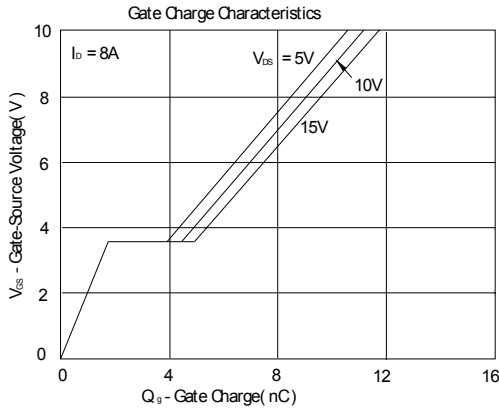
Characteristic Curves

N-Channel





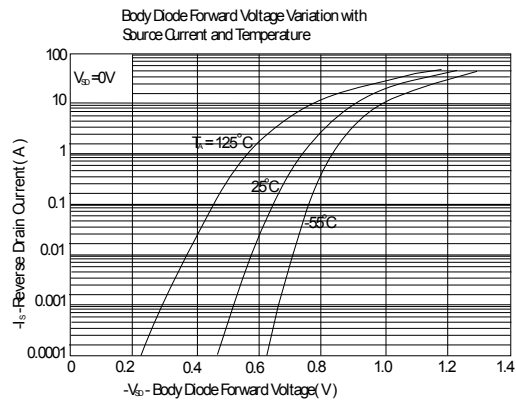
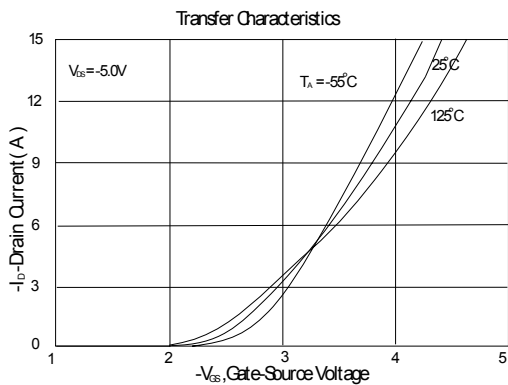
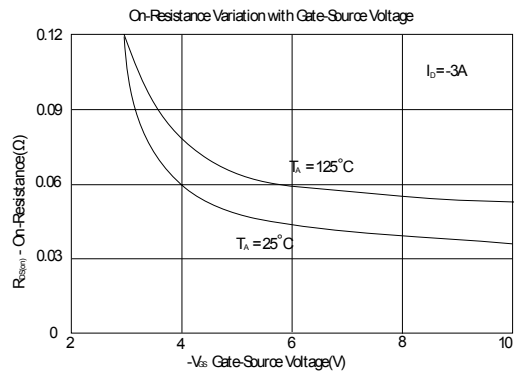
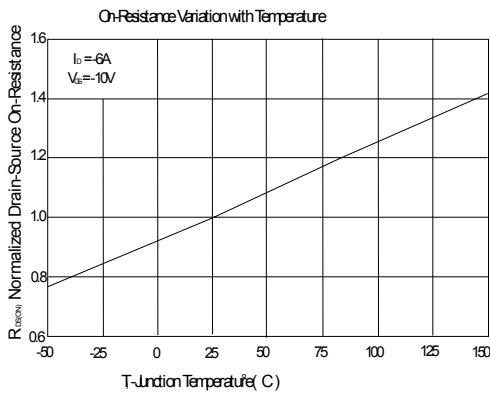
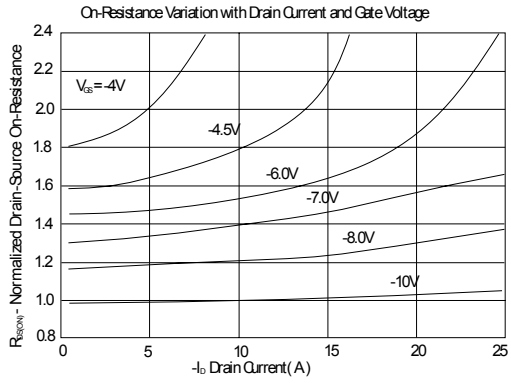
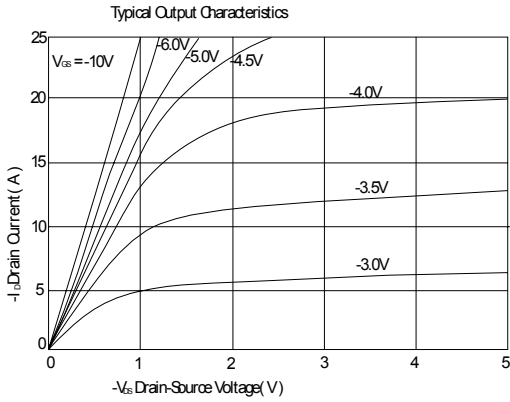
Characteristic Curves(Cont.)





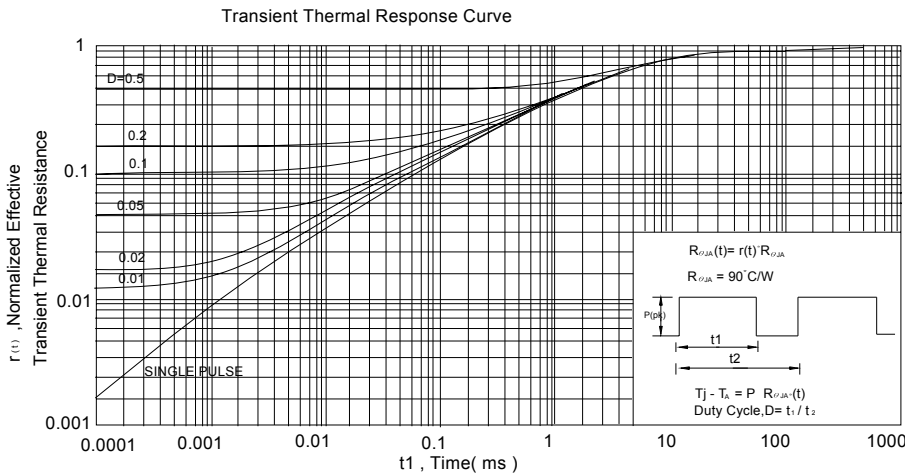
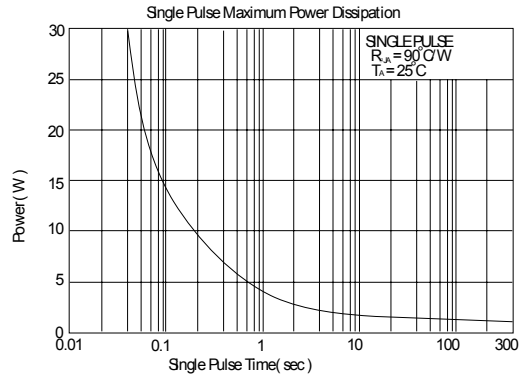
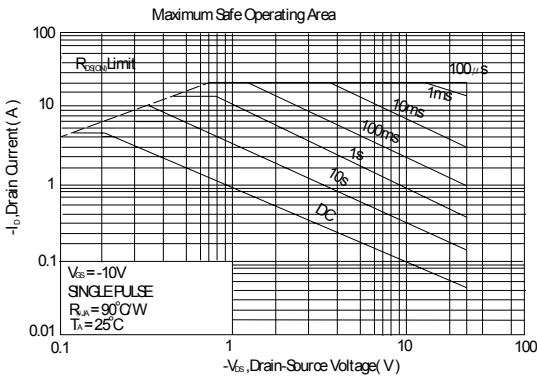
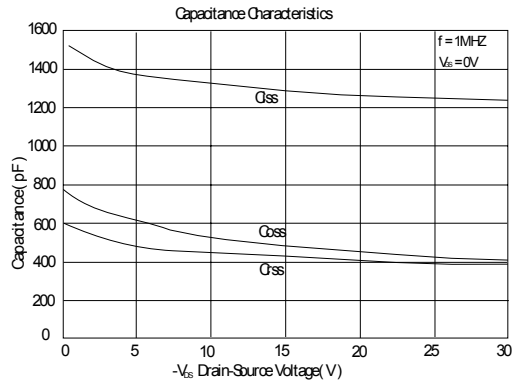
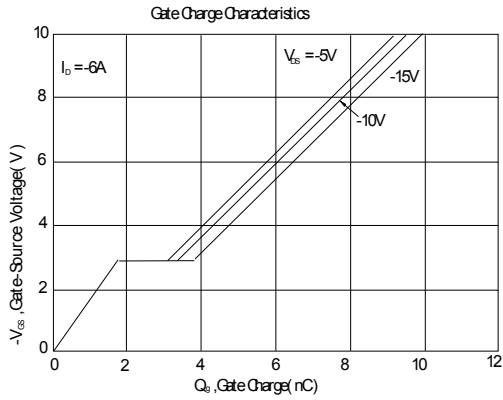
Characteristic Curves(Cont.)

P-Channel

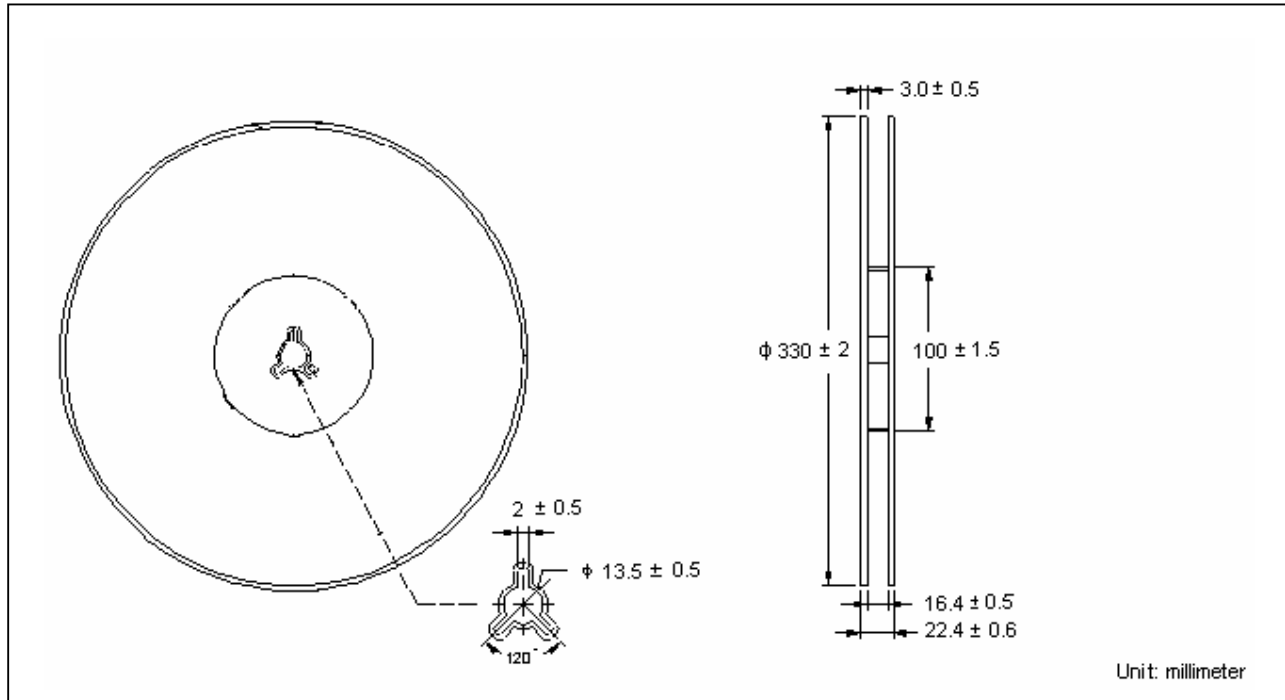




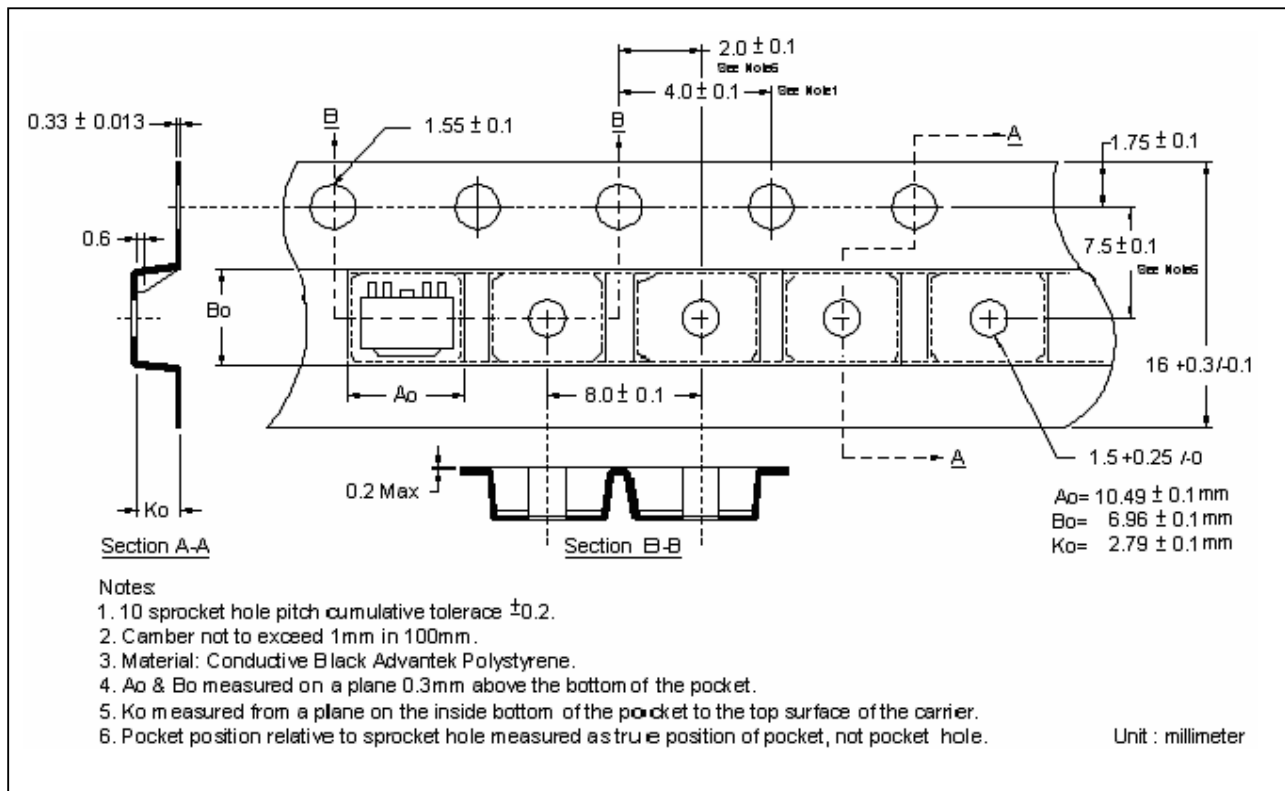
Characteristic Curves(Cont.)



Reel Dimension

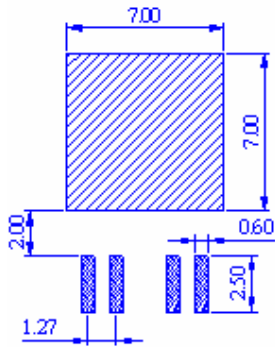


Carrier Tape Dimension





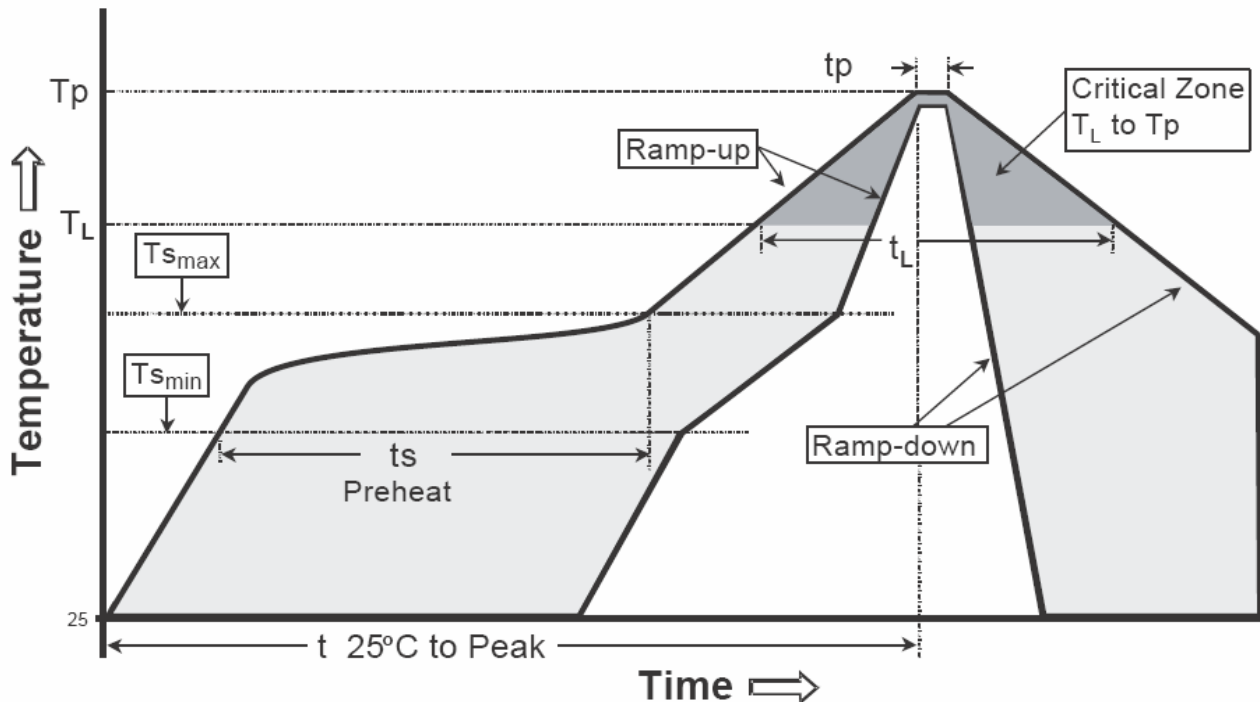
Recommended soldering footprint



Unit : mm

Recommended wave soldering condition

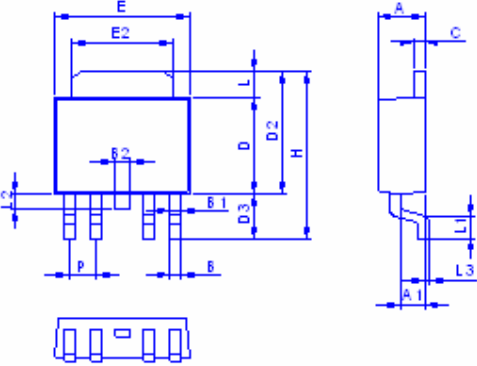
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


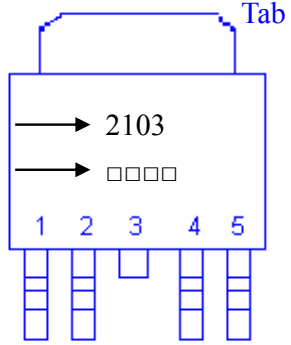
Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _s min)	100°C	150°C
-Temperature Max(T _s max)	150°C	200°C
-Time(t _s min to t _s max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



Marking:



Device Name → 2103
 Date code → □□□□

1 2 3 4 5

Tab

Style: Pin 1.Soure 1 2.Gate 1 3.&Tab
 Drain 1& Drain 2 4. Source 2 5. Gate 2

4-Lead TO-252 Plastic Surface Mount Package
 CYStek Package Code: J4

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0826	0.0984	2.10	2.50	E	0.2480	0.2638	6.30	6.70
A1	0.0433	0.0512	1.10	1.30	E2	0.1890	0.2146	4.80	5.45
B	0.0118	0.0276	0.30	0.70	H	0.3622	0.3996	9.20	10.15
B1	0.0217	0.0295	0.55	0.75	L	0.0512	0.0669	1.30	1.70
B2	0.0157	0.0315	0.40	0.80	L1	0.0354	0.0590	0.90	1.50
C	0.157	0.0236	0.40	0.60	L2	0.0197	0.0433	0.50	1.10
D	0.2087	0.2244	5.30	5.70	L3	0.0000	0.0118	0.00	0.30
D2	0.2638	0.2874	6.70	7.30	P	0.0461	0.0539	1.17	1.37
D3	0.0866	0.1181	2.20	3.00					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : KFC; Pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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